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2D XY Ordering in Striped CuO_2 Planes in Underdoped $Bi_2Sr_2CaCu_2O_{8+\delta}$

G.G.Sergeeva

Abstract

It was discussed the possibility of determination of the temperature of 2D XY ordering, T_{BKT}, in striped CuO_2 planes for quasi-two dimensional HTS with the semiconducting behavior of the out-of-plane resistivity $\rho_c(T)$ in normal state. From the results of measurements $\rho_c(T)$ [1] for samples of underdoped $Bi_2Sr_2CaCu_2O_{8+\delta}$ the values of T_{BKT} were found out [2]. Its are compared with results of measurements of frequency dependent conductivity $\sigma(\omega)$[3]. It is shown that these both results give close value of $T_{BKT} \sim 62K$ for samples with $T_c = 74K$, and verify the importance of taken into account two-dimensional fluctuations effects at $T > T_c$.

National science center "Kharkov Institute of Physics and Technology",
Academicheskaya st. 1, 61108, Kharkov, Ukraine

The hypothesis that the the semiconducting behavior of the out-of-plane resistivity $\rho_c(T)$ in quasi-two dimensional HTS is the result of strong two-dimensional antiferromagnetic (AFM) and superconducting fluctuations in striped CuO_2 planes (with metallic and insulating stripes) at $T_c < T < T^*$ was discussed in Refs. [2,4] (here T^* is the charge ordering temperature). In the region, where ρ_c exceeds the Mott limit $\rho_M \sim 10^{-2}\Omega \cdot cm$, the charge transport along axis $\widehat{c}$ can be treated as a process of tunneling through a nonconducting barrier with temperature depending probability $t_c(T) \sim |\xi_c(T)/\xi_{ab}(T)|^2$:

$$\rho_c \simeq \rho_M (N_0 t_c)^{-1} \tag{1}$$

where N_0 is the density states in the CuO_2 plane, $\xi_{ab}(T)$ and $\xi_c(T)$ are the correlations lengths in the CuO_2 plane and along axis $\widehat{c}$, respectively. The coexisting superconducting, dielectric and metallic regions in striped CuO_2 planes at $T_c < T < T^*$ leads to different paths of out-of-plane charge tunneling and to different temperature dependencies of the correlations lengths $\xi_{ab}(T)$ and $\xi_c(T)$. In the temperature regions $T \gg T_{BKT}$, where ξ_c does not depends on temparature and $\xi_{ab}(T)$ became formed by Ginzburg-Landau dependence $\xi_{ab}(T) = \xi_{ab}(T/T_{BKT} - 1)^{-1/2}$, it follows [2]:

$$\rho_c(T) = T_{BKT} \frac{\rho_M \xi_{ab}^2}{N_0 \xi_c^2} (T - T_{BKT})^{-1}, \tag{2}$$

where ξ_{ab} and ξ_c are the values of the correlations lengths at T_{BKT}. Measurements of $\rho_c(T)$ [1] allows us to determine T_{BKT} without any fitting parameter:

$$T_{BKT} = \frac{\rho_i T_i - \rho_k T_k}{\rho_i - \rho_k}, \tag{3}$$

where pair points T_i, T_k on curve $\rho_c(T)$ are taken approximately on 15 - 20K above the temperature, where semiconducting trend of ρ_c end off at low temperatures. The calculations of averaged values $\overline{T_{BKT}}$ for four pairs points T_i, T_k lead to the following results: $61.72K, \quad 60.62K, \quad 56.2K, \quad 47.92K$, respectively for samples with δ, which are equals $0.2135, \quad 0.216, \quad 0.22, \quad 0.23$.

The dependence (2) with calculated $\overline{T_{BKT}}$ well describes the results of the measurements of out-of-plane resistivity for single crystalls Bi-2212 [1] in normal state in enough big temperature interval, $96K + \Delta T_{fl}$, which is beginning at nearly undependent on oxygen concentration δ temperature $96K$. ΔT_{fl} is depending on δ and is changing from 24 K at $\delta = 0.23$ up to 104 K at $\delta = 0.2135$ [2]. It is seen that values T_{BKT} and ΔT_{fl} for samples are increasing at decreasing oxygen concentration.

It is very interesting to compare these results with the measurements of frequency dependent conductivity, $\sigma(\omega, T)$, for epitaxial films of underdoped $Bi_2Sr_2CaCu_2O_{8+\delta}$ with $T_c = 74K$ (see fig.2 from ref.[3]). The temperature of two-dimensional melting, T_{BKT}, determines as the temperature of the crossover of two curves, namely $(\hbar\omega/k_B\sigma_Q)\sigma_2(\omega, T)$ and universal line $(8/\pi)T$ [5](here $\sigma_Q = e^2/\hbar d$ is quantum conductivity of a stack of planar conductors with interlayer spacing d, $\sigma_2(\omega, T)$ is imaginary part of conductivity $\sigma(\omega, T)$. It is seen from fig.2 [3], that this crossover occurs at temperature 62 K, which is limiting the region of frequency independent conductivity σ_2. As we see from results of refs.[1,2], the samples with $T_c \simeq 74K$ have $\delta = 0.2135$ and $T_{BKT} \simeq 61.72K$. Thus, we can say that at $T \geqslant 62K$ first unbound vortices appear that leads to the observation of frequency dependent conductivity $\sigma_2(\omega, T)$ and to exponential dependence $\rho_c(T)$ at $T_c < T < 95K$ [2].

¿From the comparison of the results of refs.[1,2] and [3] it follows that the region of the temperatures, $62K < T < 95K$, where the contribution in short-timescale dynamics of thermally generated vortices is distinguishable from another contributions, coincides for both measurements. However in underdoped HTS, forceful evidences for some form of pairing are found up to the temperature T^* as in spectroscopic measurements [6], so as both in resistivity measurements [1,2] and in measurements of Knight shift [7-8]. Now the question is under the discussion: which is just form of pairing without phase coherence in the region $T^* > T > 95K$? It can be or d-wave pairing of normal electrons with momentum for which superconducting gap vanishes [9], and or pairing in striped CuO_2 planes, which leads to two-dimensional superconducting fluctuations in the theory Ginzburg-Landau (see expression (3) and ref.[2]).

References

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